YUYUE

20N65F

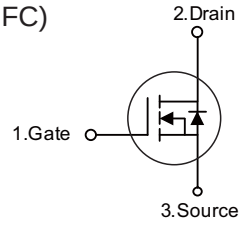
N-Channel Enhancement Mode MOSFET

Features

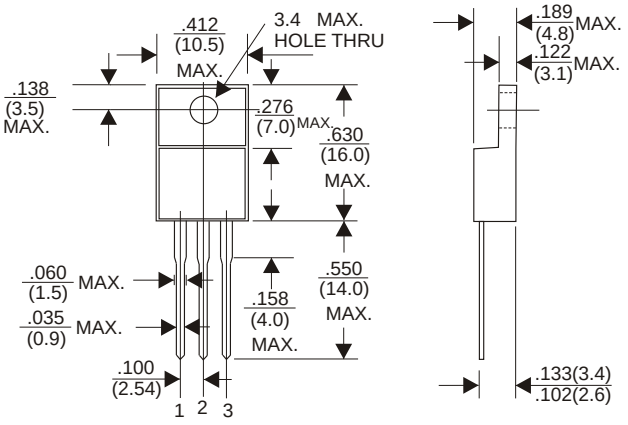
- 650V,20A
- $R_{DS(ON)}$ = 0.35Ω (Typ.) @ V_{GS} = 10V, I_D =10A
- Fast Switching
- Improved dv/dt Capability
- 100% Avalanche Tested

Application

- Switch Mode Power Supply(SMPS)
- Uninterruptible Power Supply(UPS)
- Power Factor Correction (PFC)



ITO-220F (FULLYINSULATED)



Dimensions in inches and (millimeters)

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise specified)

Parameter		Symbol	20N65F		Units
Drain-Source Voltage		V_{DSS}	650		V
Gate-Source Voltage		V_{GSS}	±30		V
Continuous Drain Current	T_C = 25℃	I_D	20		A
	T_C = 100℃		13		A
Pulsed Drain Current note1		I_{DM}	80		A
Single Pulsed Avalanche Energy note2		E_{AS}	1350		mJ
Power Dissipation	T_C = 25℃	P_D	167	416	W
Thermal Resistance, Junction to Case		$R_{\theta JC}$	0.75	0.3	℃/W
Thermal Resistance, Junction to Ambient		$R_{\theta JA}$	60	60	℃/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150		℃

20N65F

Electrical Characteristics (T_C=25℃ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V,I_D=250μA	650	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 650V, V_{GS} = 0V, T_J= 25℃	-	-	1	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS} =0V, V_{GS} = ±30V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}, I_D=250μA	2	3	4	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note3	V_{GS} =10V, I_D =10A	-	0.35	0.45	Ω
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz	-	2978	-	pF
C_{oss}	Output Capacitance		-	291	-	pF
C_{rss}	Reverse Transfer Capacitance		-	40	-	pF
Q_g	Total Gate Charge	V_{DD} = 520V, I_D = 20A, V_{GS} = 10V	-	80	-	nC
Q_{gs}	Gate-Source Charge		-	12	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	34	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD} = 325V, I_D =20A, R_G = 25Ω	-	37	-	ns
t_r	Turn-on Rise Time		-	66	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	175	-	ns
t_f	Turn-off Fall Time		-	84	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	20	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	80	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_{SD} = 20A	-	-	1.4	V
t_{rr}	Reverse Recovery Time	V_{GS} =0V, I_S=20A, di/dt=100A/μs	-	450	-	ns
Q_{rr}	Reverse Recovery Charge		-	7.1	-	μC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. I_{AS} =16A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C

3. Pulse Test: Pulse Width≤350μs, Duty Cycle≤1%

RATING AND CHARACTERISTIC CURVES (20N65F)

Figure1: Output Characteristics

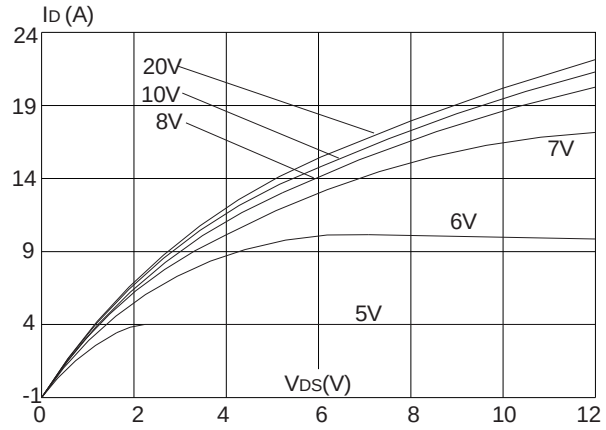


Figure 2: Typical Transfer Characteristics

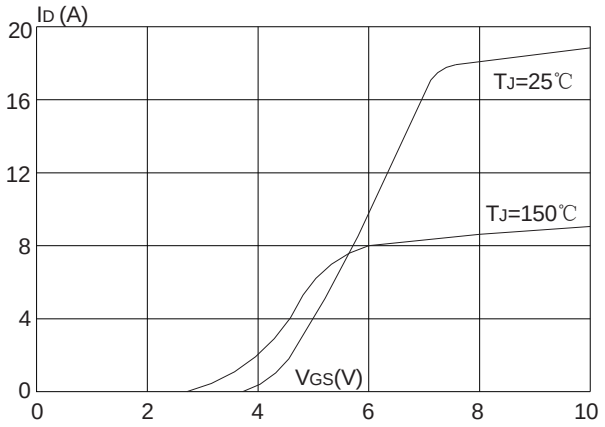


Figure 3: On-resistance vs. Drain Current

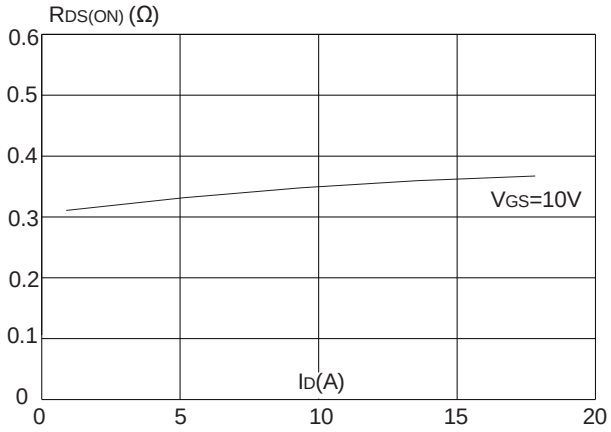


Figure 4: Body Diode Characteristics

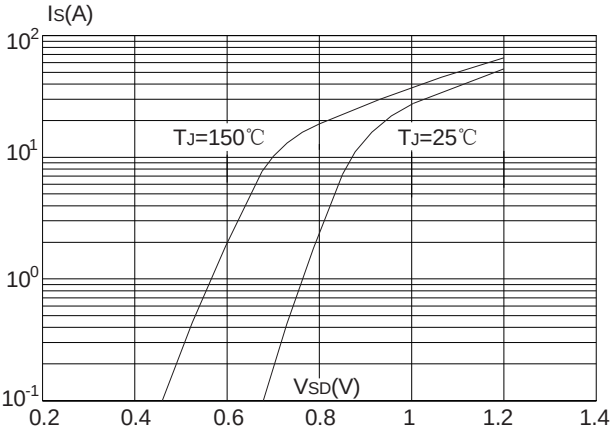


Figure 5: Gate Charge Characteristics

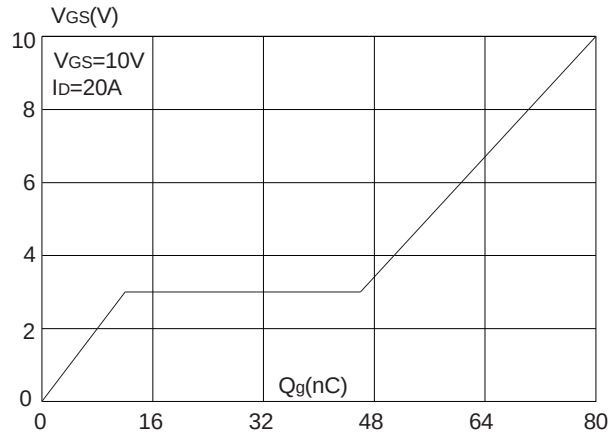
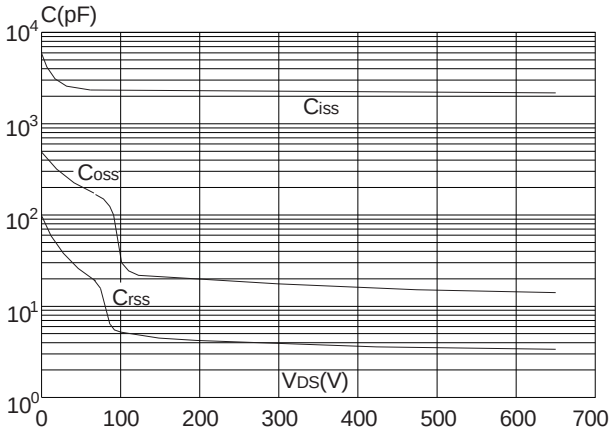


Figure 6: Capacitance Characteristics



RATING AND CHARACTERISTIC CURVES (20N65F)

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

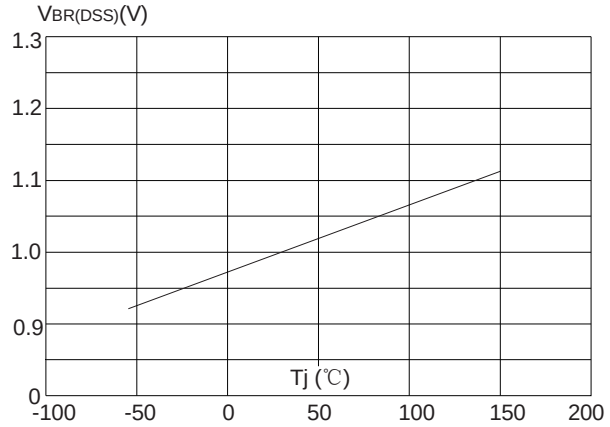


Figure 8: Normalized on Resistance vs. Junction Temperature

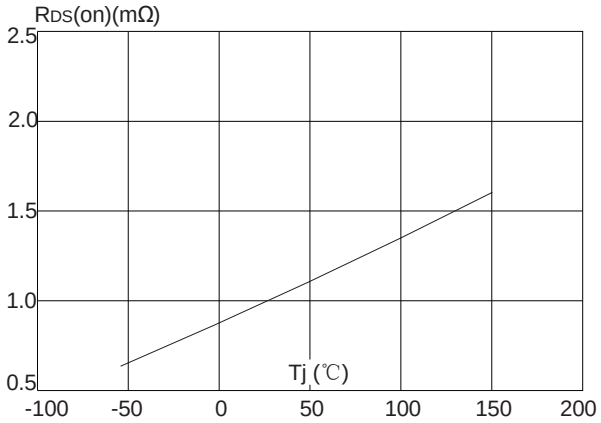


Figure 9: Maximum Safe Operating Area

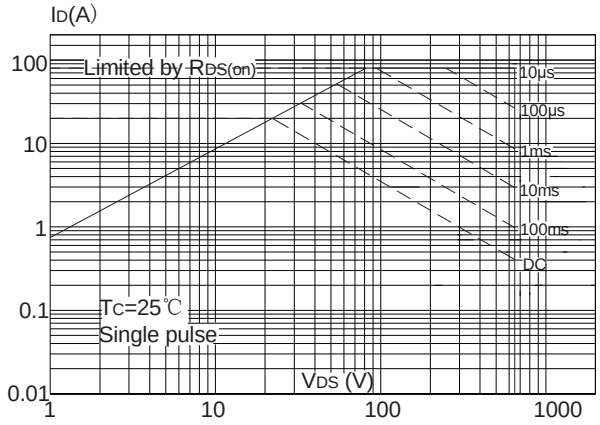


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

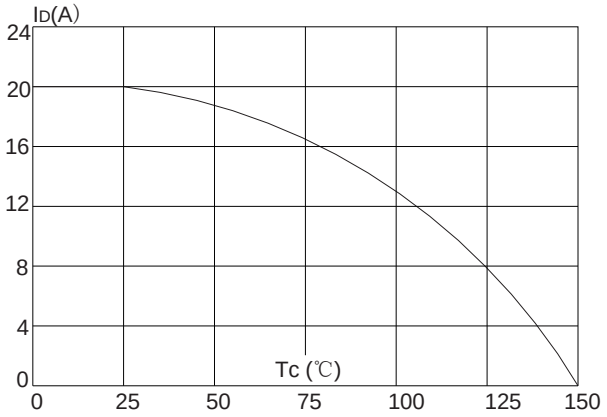


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case (TO-220F)

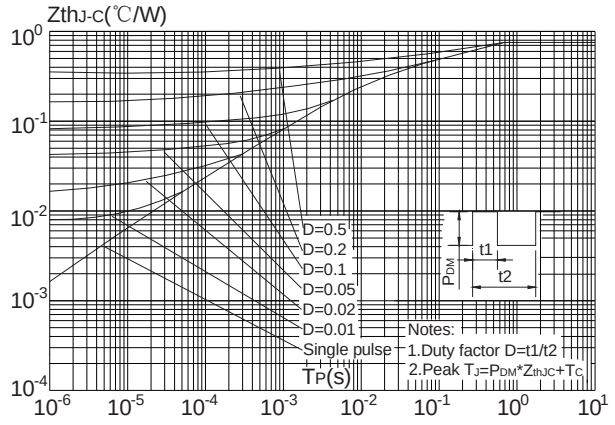


Figure.12: Maximum Effective Transient Thermal Impedance, Junction-to-Case (TO-247,TO-3P)